

## isc N-Channel MOSFET Transistor

### 2SK3592L

### **FEATURES**

- Drain Current : I<sub>D</sub>= 57A@ T<sub>C</sub>=25℃
- Drain Source Voltage : V<sub>DSS</sub>= 150V(Min)
- Static Drain-Source On-Resistance
- : R<sub>DS(on)</sub> = 41m Ω (Max) @ V<sub>GS</sub>= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRIPTION

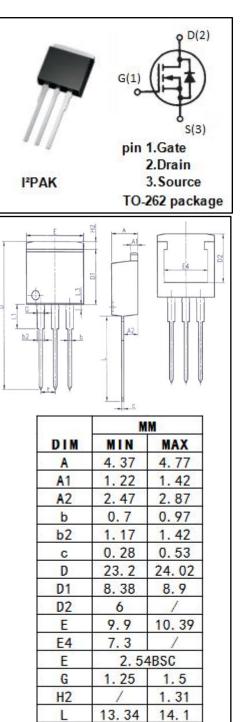
· motor drive, DC-DC converter, power switch and solenoid drive.

| ABSOLUTE MAXIMUM RATINGS(Ta=25°C) |                                     |         |      |  |  |  |
|-----------------------------------|-------------------------------------|---------|------|--|--|--|
| SYMBOL                            | PARAMETER VALUE                     |         | UNIT |  |  |  |
| V <sub>DSS</sub>                  | Drain-Source Voltage                | 150     | V    |  |  |  |
| V <sub>GS</sub>                   | Gate-Source Voltage-Continuous      | ±30     | V    |  |  |  |
| ID                                | Drain Current-Continuous            | 57      | A    |  |  |  |
| I <sub>DM</sub>                   | Drain Current-Single Pluse          | 200     | A    |  |  |  |
| PD                                | Total Dissipation @Tc=25℃           | 270     | W    |  |  |  |
| TJ                                | Max. Operating Junction Temperature | -55~150 | °C   |  |  |  |
| T <sub>stg</sub>                  | Storage Temperature -55~150         |         | °C   |  |  |  |

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### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | МАХ  | UNIT         |
|---------------------|--------------------------------------|------|--------------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 0.46 | °C <b>/W</b> |



L1

L3

3.3

0.95

4.06

1.15



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS                                     | MIN | МАХ  | UNIT |
|----------------------|---------------------------------|--|-----|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA   | 150 |      | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = 10V; I <sub>D</sub> = 0.25mA | 3   | 5    | V    |
| R <sub>DS</sub> (on) | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 20A    |     | 41   | mΩ   |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0      |     | ±0.1 | uA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 150V; V <sub>GS</sub> = 0    |     | 25   | uA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 40A; V <sub>GS</sub> = 0      |     | 1.65 | V    |

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